

科目可使用計算機\*

- 1(25%) The circuit shown in Fig. 1 implements one form of a difference amplifier. Assuming that  $R_1=5k\Omega$ ,  $R_2=20k\Omega$ ,  $R_3=4k\Omega$ ,  $R_4=50k\Omega$ , and all three op amps are ideal, determine the output  $v_o$  in terms of the inputs  $v_{i1}$  and  $v_{i2}$ , then determine the differential input resistance  $R_{id}$  between  $v_{i1}$  and  $v_{i2}$ .

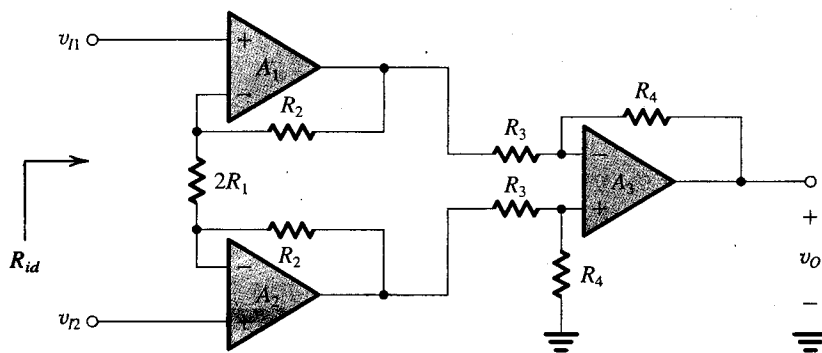
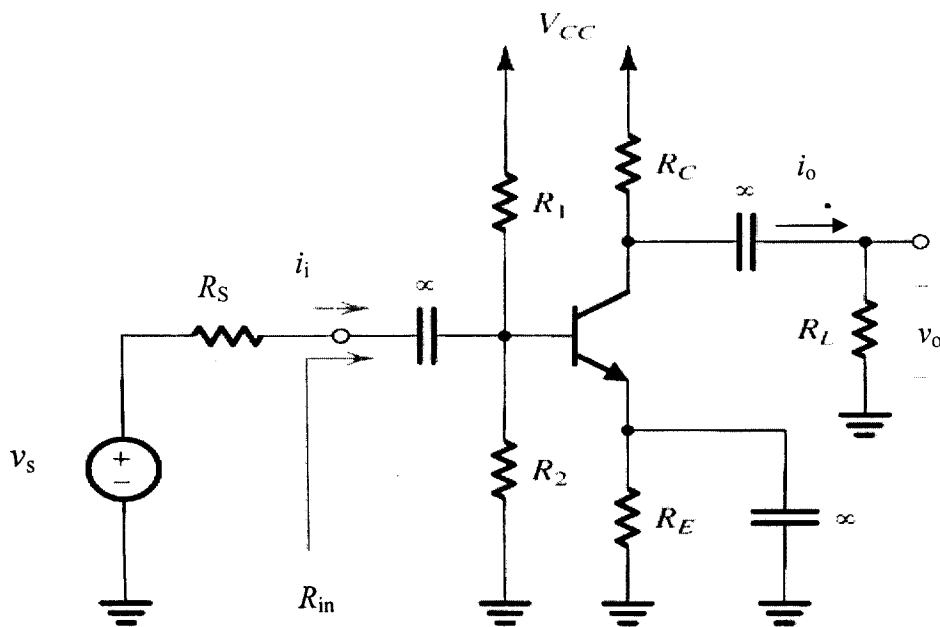


Fig. 1

- 2(25%) Please depict the circuit symbol of a diode, with a forward current  $i$  through it and the voltage drop  $v$  across it. It is known that the relationship between  $i$  and  $v$  can be expressed as  $i=I_s \exp(v/nv_T)$ . Depict its  $i$ - $v$  characteristics for  $i>0$ . It is further known that a particular diode displays a forward voltage of  $0.704V$  at a forward current of  $1mA$ , and have a  $0.096V/decade$  current change characteristics. Determine its voltage drop at a forward current of  $0.751mA$ .
- 3(25%) For the common-emitter amplifier shown in Fig. 3, let  $V_{CC} = 9V$ ,  $R_S = 10 k\Omega$ ,  $R_L = 2 k\Omega$ ,  $R_1 = 27 k\Omega$ ,  $R_2 = 15 k\Omega$ ,  $R_E = 1.2 k\Omega$ , and  $R_C = 2.2 k\Omega$ . The transistor has  $\beta = 100$  and  $V_A = 100 V$ .
- Calculate the dc emitter current  $I_E$ .
  - Replace the transistor with its hybrid- $\pi$  model, and draw the small-signal equivalent circuit of Fig. 3.
  - Find the input resistance  $R_{in}$ .
  - Determine the voltage gain  $v_o/v_s$ .
  - Find the current gain  $i_o/i_i$ .



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- 4(25%) Using two transistors  $Q_1$  and  $Q_2$  having equal lengths but widths related by  $W_2/W_1 = 5$ , design the circuit of Fig. 4(b) to obtain  $I = 0.5$  mA. Let  $V_{DD} = V_{SS} = 5$  V,  $\mu_n C_{ox}(W/L)_1 = 0.8$  mA/V<sup>2</sup>,  $V_t = 1$  V, and  $\lambda = 0$ .
- Find the required value for  $R$ .
  - What is the voltage at the gates of  $Q_1$  and  $Q_2$ ?
  - What is the lowest voltage allowed at the drain of  $Q_2$  while  $Q_2$  remains in the saturation region?
  - If the circuits of Fig. 4 are implemented in integrated circuit (IC) form, which transistor(s) ( $Q$ ,  $Q_1$ , or  $Q_2$ ) will suffer from the body effect? Why?

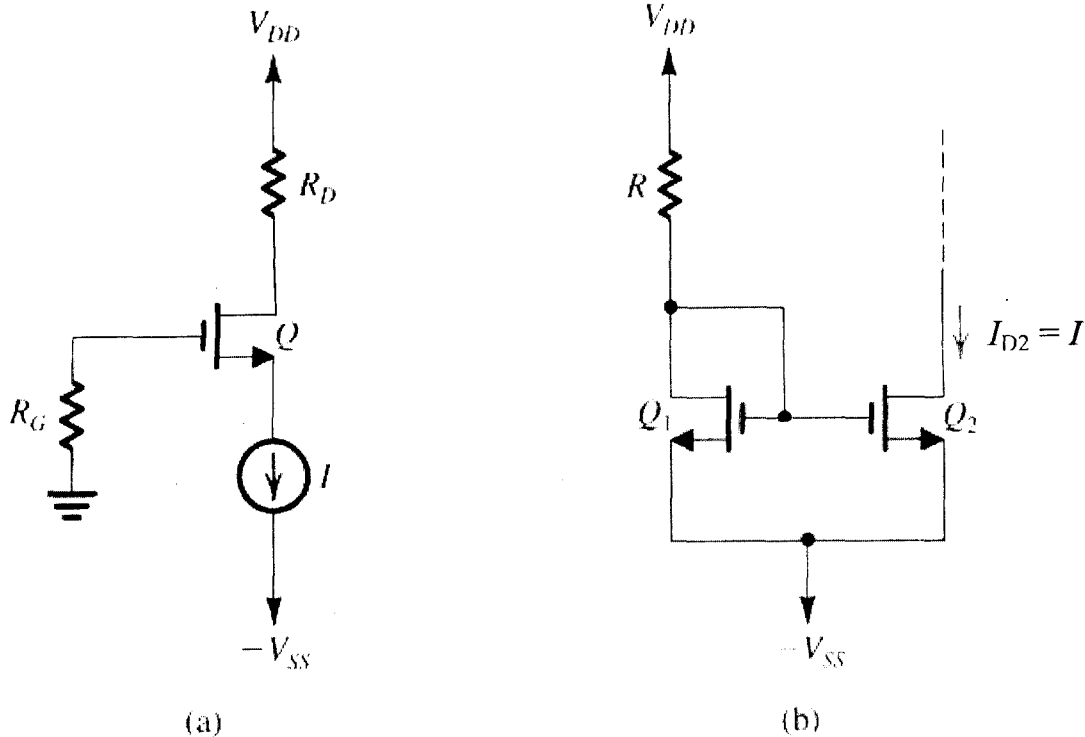


Figure 4 (a) Biasing the MOSFET using a constant-current source  $I$ .

(b) Implementation of the constant-current source  $I$  using a current mirror.